TEXAS INSTRUMENTS

CD74HCT242, CD74HC243, CD74HCT243

Data sheet acquired from Harris Semiconductor
SCHS168

November 1997

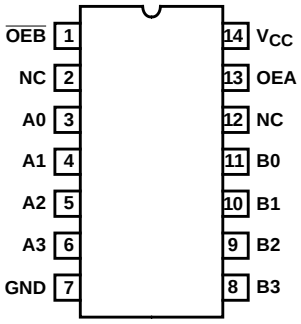
High Speed CMOS Logic
Quad-Bus Transceiver with Three-State Outputs

Features

- **Typical Propagation Delay (A to B, B to A) of 7ns at V_{CC} = 5V, C_L = 15pF, T_A = 25°C**
- **Three-State Outputs**
- **Buffered Inputs**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55°C to 125°C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Pinout

CD74HCT242, CD74HC243, CD74HCT243
(PDIP, SOIC)
TOP VIEW



Description

The Harris CD74HCT242, CD74HC243 and CD74HCT243 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads.

The CD74HCT242 is an inverting buffer; the CD74HC243 and CD74HCT243 are non-inverting buffers.

The states of the output enables ($\overline{OEB}$, OEA) determine both the direction of flow (A to B, B to A), and the three-state mode.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC243E	-55 to 125	14 Ld PDIP	E14.3
CD74HC243M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT243M	-55 to 125	14 Ld SOIC	M14.15

NOTES:

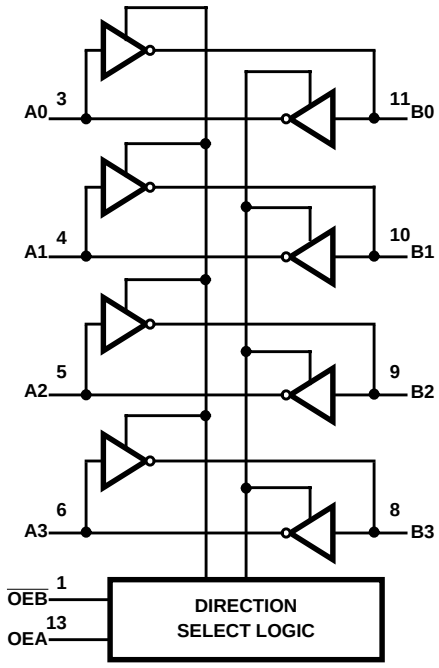
1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

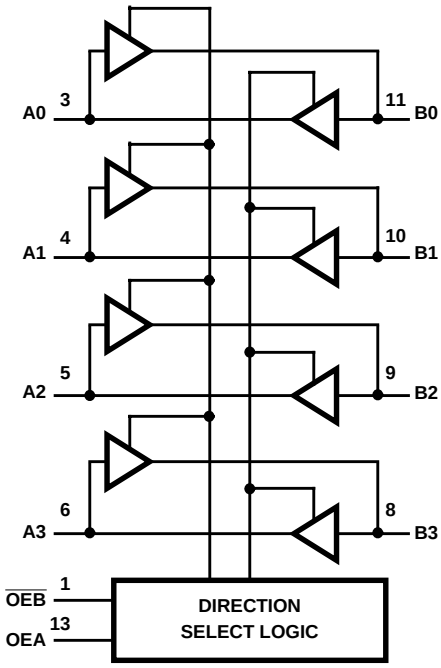
File Number **1488.1**

Functional Diagrams

CD74HCT242



CD74HC243, CD74HC243



TRUTH TABLE

CONTROL INPUTS		HCT242 SERIES DATA PORT STATUS		HC, HCT243 SERIES DATA PORT STATUS	
$\overline{OEB}$	OEA	An	Bn	An	Bn
H	H	$\overline{O}$	I	O	I
L	H	Z	Z	Z	Z
H	L	Z	Z	Z	Z
L	L	I	$\overline{O}$	I	O

NOTE:
H = High Voltage Level
L = Low Voltage Level
I = Input
O = Output (Same Level as Input)
$\overline{O}$ = Output (Inversion of Input Level)
Z = High Impedance
To prevent excess currents in the High Z modes all I/O terminals should be terminated with 10kΩ to 1MΩ resistors.

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} + 0.5V . . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . . ±70mA

Operating Conditions

Temperature Range (T_A) . . . . . -55°C to 125°C
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3) θ_{JA} (°C/W)
PDIP Package 90
SOIC Package 175
Maximum Junction Temperature . . . . . 150°C
Maximum Storage Temperature Range . . . . . -65°C to 150°C
Maximum Lead Temperature (Soldering 10s) . . . . . 300°C
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	-	6	-	-	±0.5	-	±0.5	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	-	5.5	-	-	±0.5	-	±5.0	-	±10	µA

NOTE:

4. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
An, Bn	1.1
OEA, $\overline{OEB}$	0.6

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360µA max at 25°C.

Switching Specifications Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay Data to Outputs (HC243)	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	90	115	135	ns
			4.5	-	18	23	27	ns
		C_L = 15pF	5	7	-	-	-	ns
		CL = 50pF	6	-	15	20	23	ns
Output High-Z, to High Level to Low Level	t_{PZL}, t_{PZH}	C_L = 50pF	2	-	150	190	225	ns
		CL = 50pF	4.5	-	30	38	45	ns
		CL = 15pF	5	12	-	-	-	ns
		CL = 50pF	6	-	26	33	38	ns
Output High Level, Output Low Level to High-Z	t_{PHZ}, t_{PLZ}	C_L = 50pF	2	-	150	190	225	ns
		CL = 50pF	4.5	-	30	38	45	ns
		CL = 15pF	5	12	-	-	-	ns
		CL = 50pF	6	-	26	33	38	ns
Output Transition Times	t_{TLH}, t_{THL}	C_L = 50pF	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (HC243) (Notes 5, 6)	C_{PD}	-	5	80	-	-	-	pF
HCT TYPES								
Propagation Delay Data to Outputs (HCT242)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	20	25	30	ns
		C_L = 15pF	5	8	-	-	-	ns
Propagation Delay Data to Outputs (HCT243)	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	22	28	33	ns
		C_L = 15pF	5	9	-	-	-	ns
Output High-Z to High Level to Low Level	t_{PZH}, t_{PZL}	C_L = 50pF	4.5	-	34	43	51	ns
		C_L = 15pF	5	14	-	-	-	ns
Output High Level, Output Low Level to High-Z	t_{PHZ}, t_{PLZ}	C_L = 50pF	4.5	-	35	44	53	ns
		C_L = 15pF	5	14	-	-	-	ns
Output Transition Times	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	12	15	18	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	HCT242	5	90	-	-	-	pF
		HCT243	5	91	-	-	-	pF

NOTES:

5. C_{PD} is used to determine the dynamic power consumption, per channel.
6. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

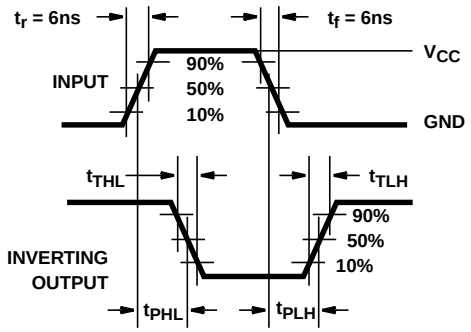


FIGURE 1. HC AND HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

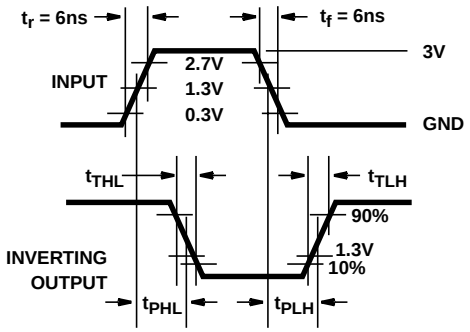


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

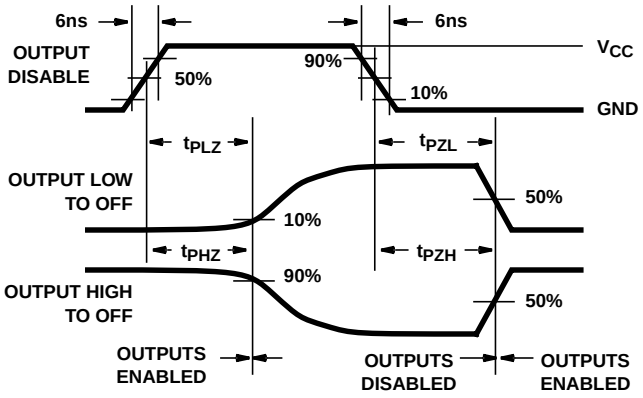


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

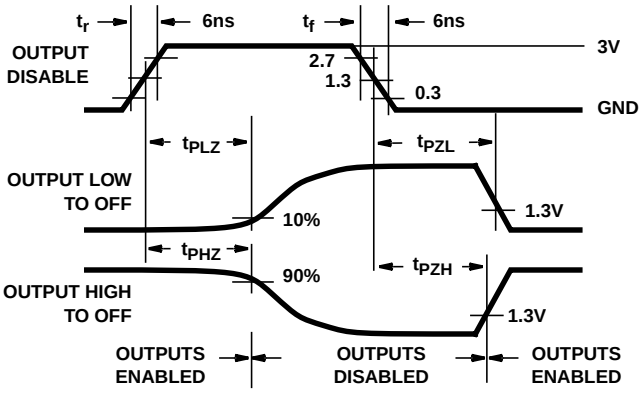
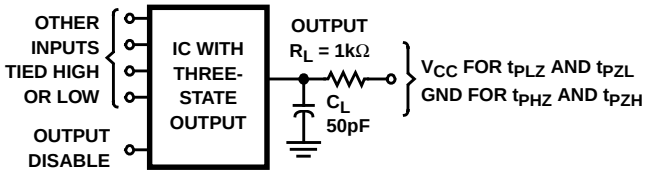


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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